

Update on sensor tests

Liaoshan Shi

Mar. 14, 2019

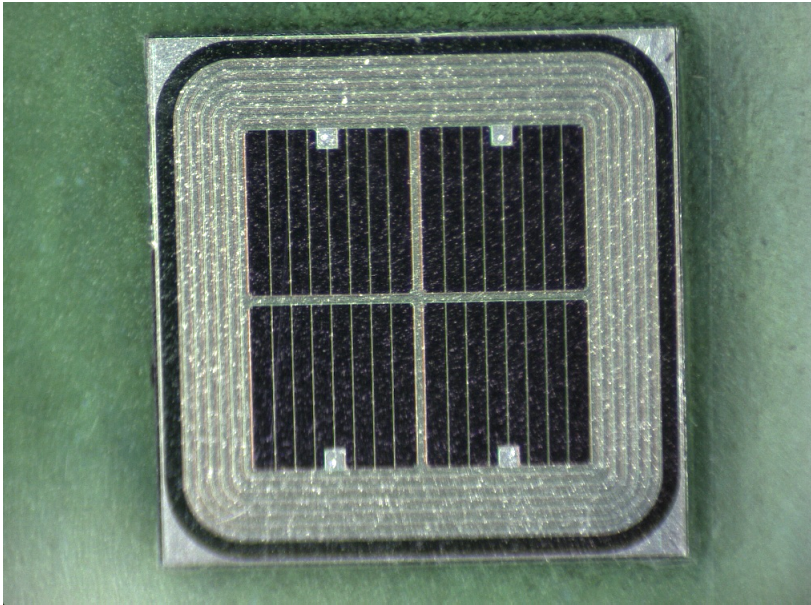
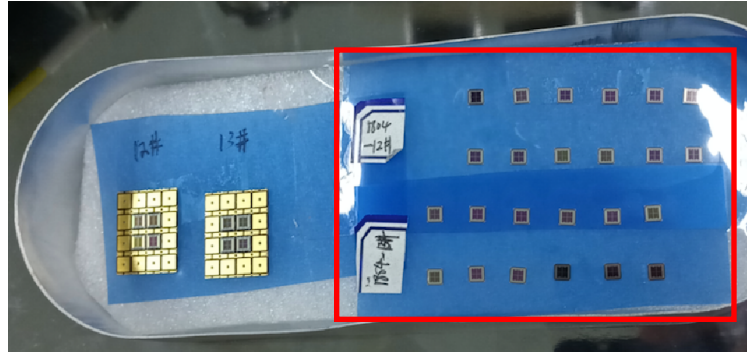
New LGAD sensors from Beijing Normal University

送货单

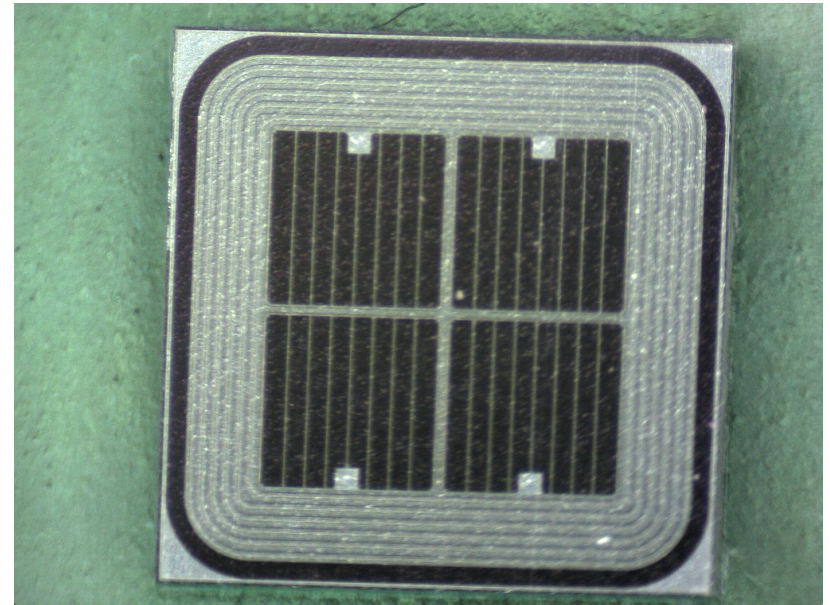
产品名称	数量	描述
BV60-50-S (12#)	16 只	(LGAD), 击穿电压~60V
BV60-50-B (1804-12#)	48 只	(LGAD), 击穿电压~60V
BV170-30-S (13#)	16 只	(LGAD), 击穿电压~170V
BV170-30-B (1804-13#)	48 只	(LGAD), 击穿电压~170V



New LGAD sensors from Beijing Normal University

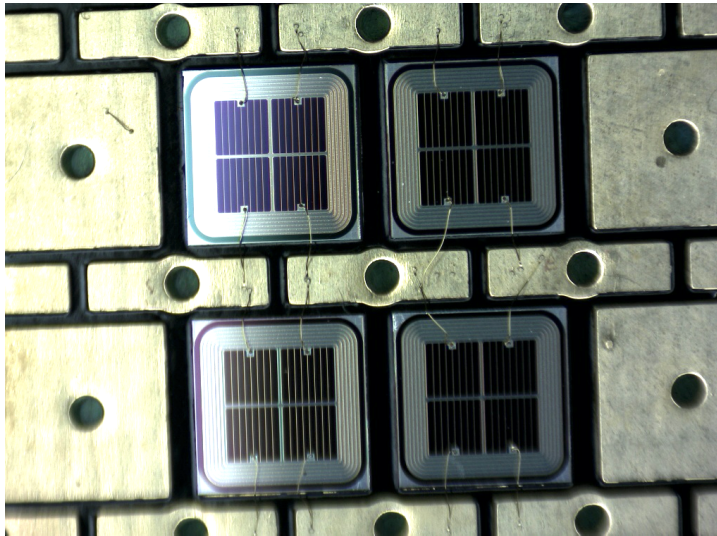
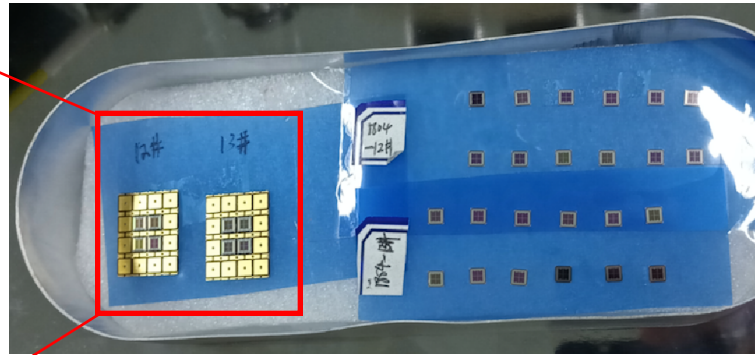
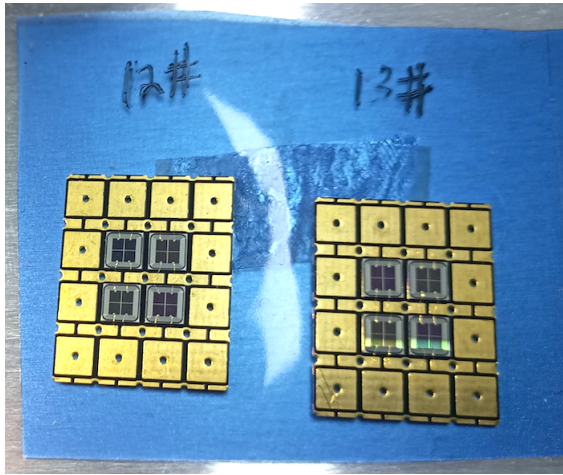


BV60-50-B

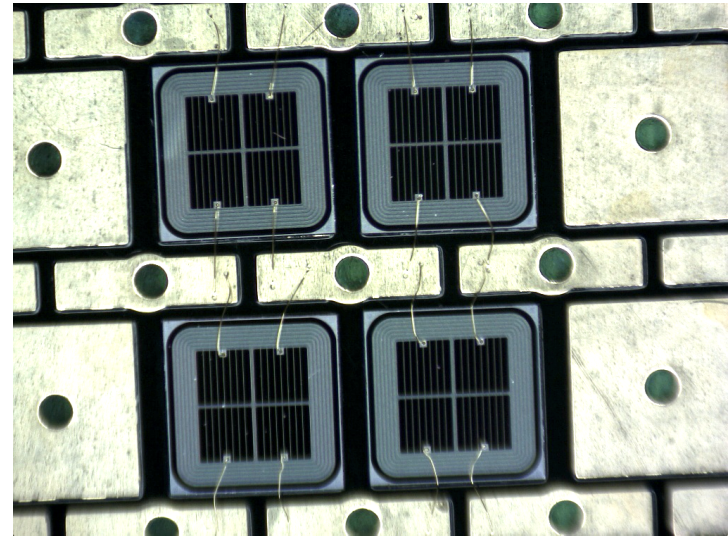


BV170-30-B

New LGAD sensors from Beijing Normal University



BV60-50-S

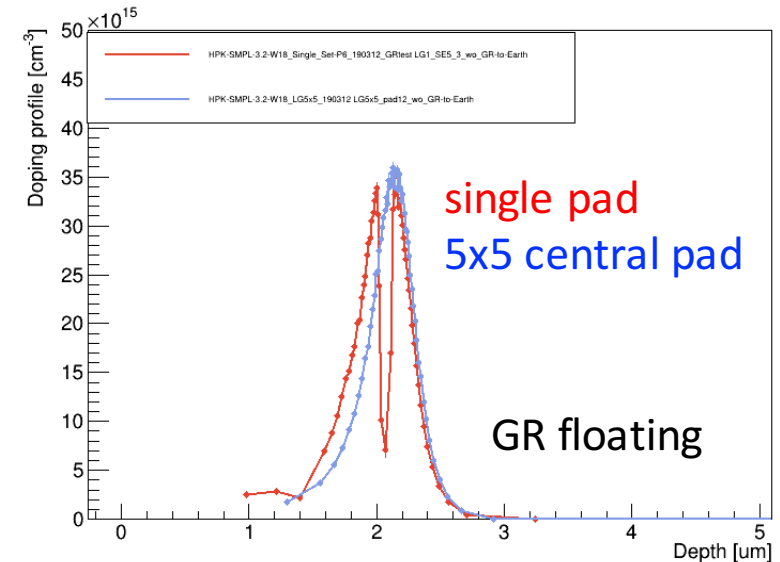
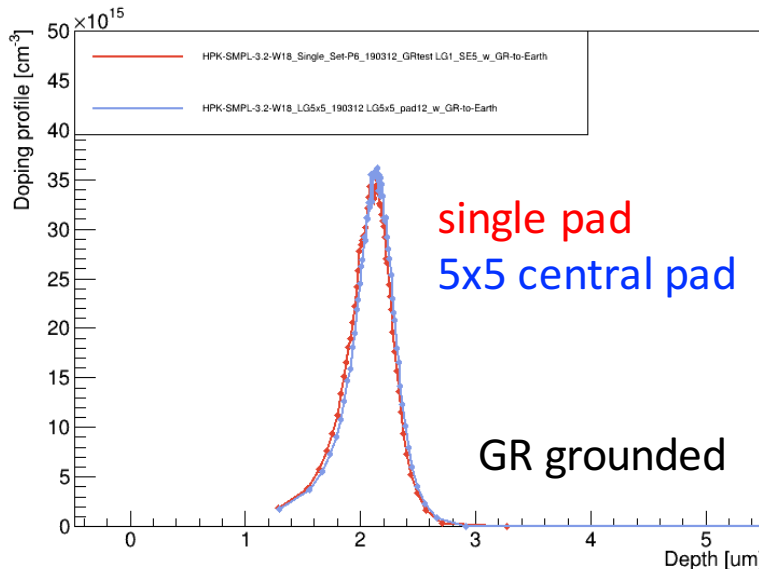
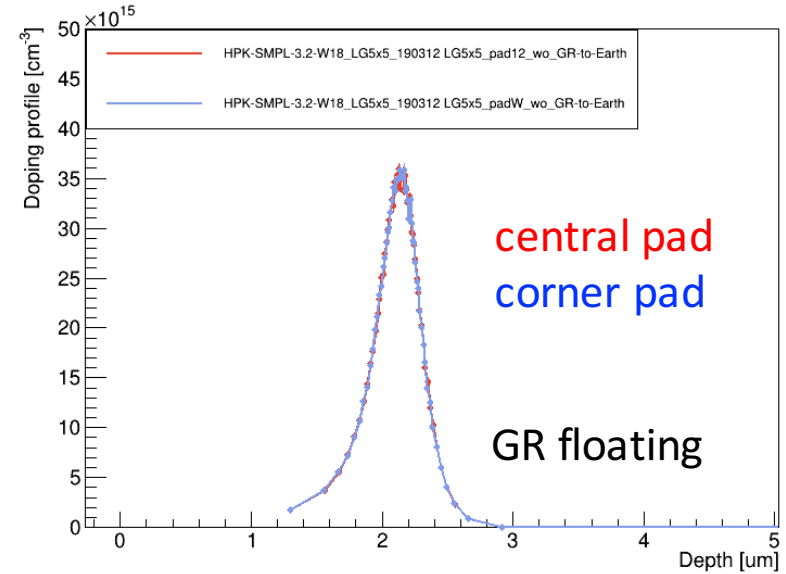
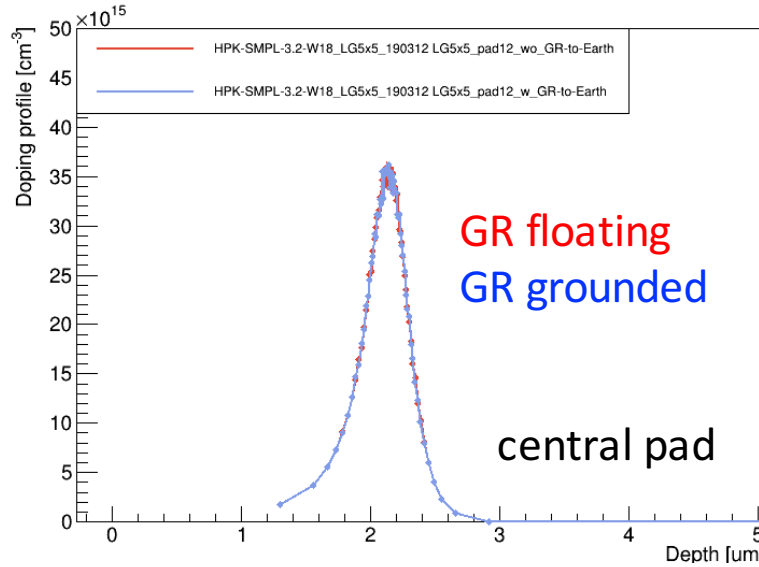


BV170-30-S

Updates on CV tests:
W18 (VBD 120V)

Doping from 5x5 array

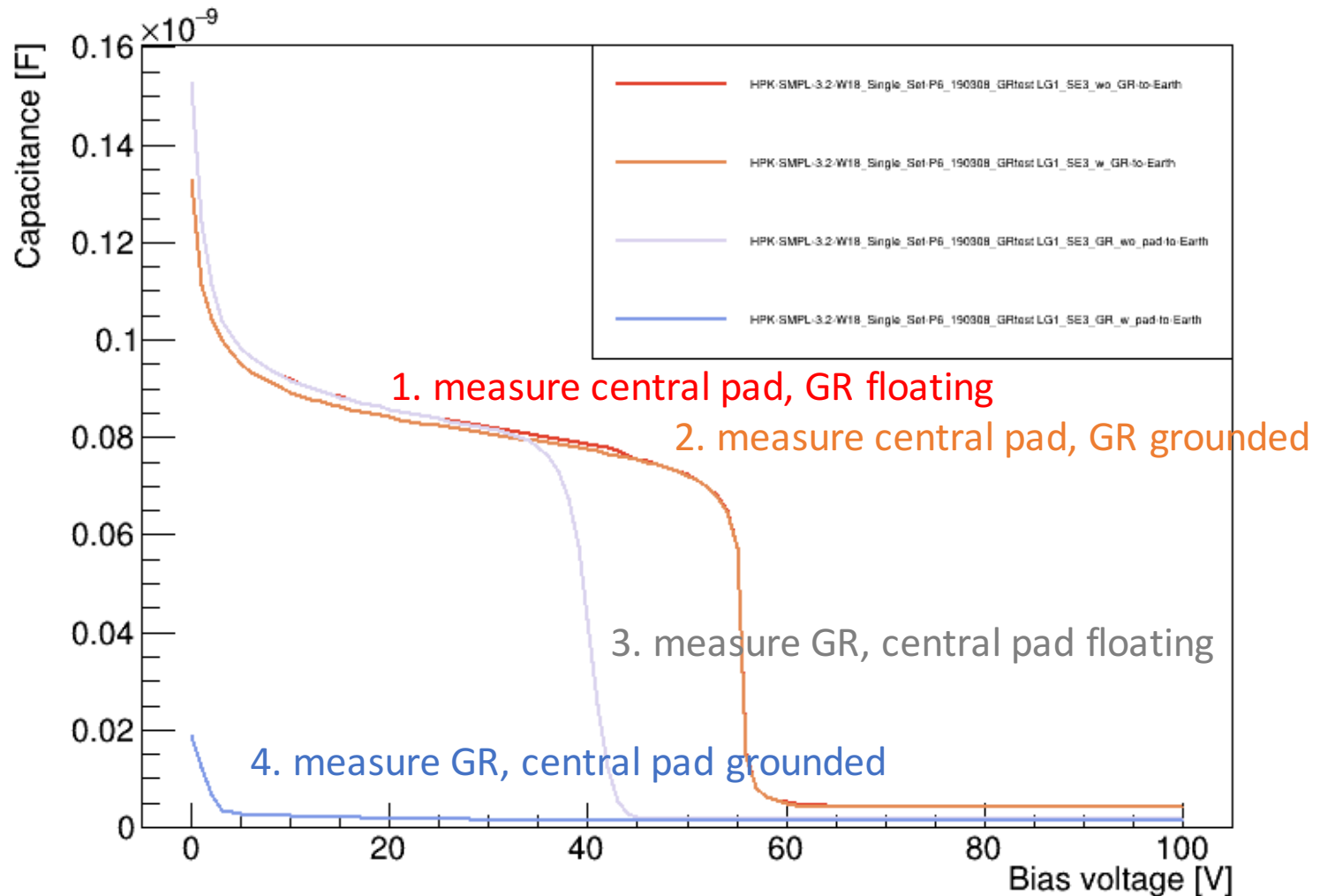
- Assume $A=0.13 \times 0.13 \text{ cm}^2$



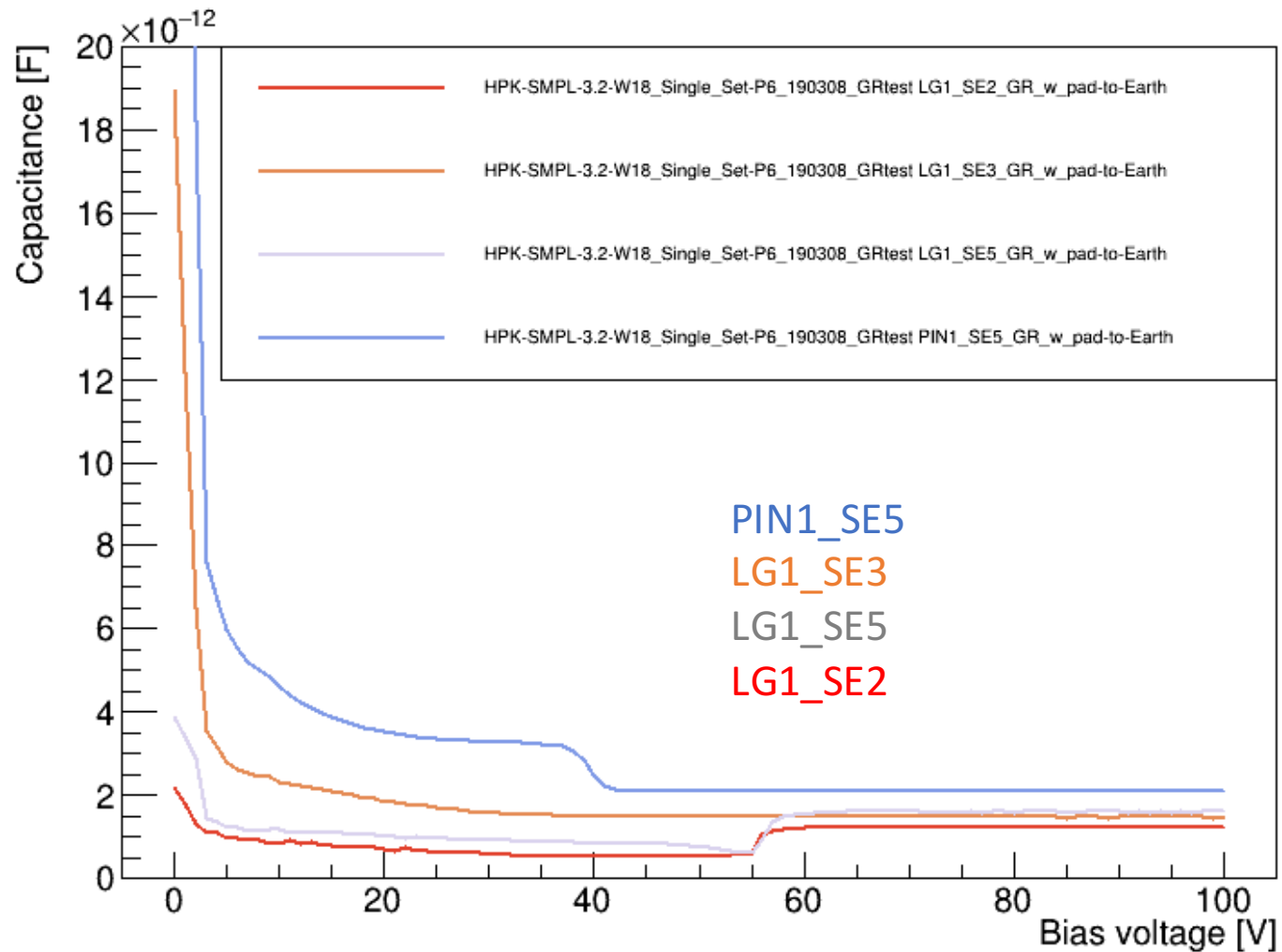
CV tests with different configurations

- Five connection schemes:
 - Measurement on sensor active area:
 1. Central pad to LCR, Guard ring floating
 2. Central pad to LCR, Guard ring to ground
 - Measurement on guard ring:
 3. Guard ring to LCR, central pad floating
 4. Guard ring to LCR, central pad to ground
 - Measurement between sensor active area and GR:
 5. Guard ring to LCR Hi, central pad to LCR Lo. The back of the sensor is floating.

CV tests with different configurations



4. measure GR, central pad grounded



5. GR to LCR Hi, central pad to LCR Lo

Bias voltage [V]	Current [uA]
-0.10	-5.2
-0.05	-2.8
0.00	-0.6
+0.05	2.0

- Capacitance below 1pF.
- Similar to a resistor of 20k Ω